AO4453

12V P-Channel MOSFET

General Description

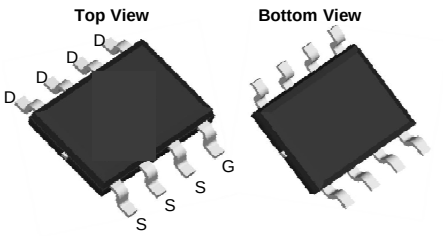
The AO4453 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

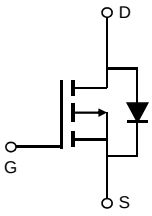
Product Summary

V_{DS}	-12V
I_D (at V_{GS}=-4.5V)	-9A
$R_{DS(ON)}$ (at V_{GS} =-4.5V)	< 19mΩ
$R_{DS(ON)}$ (at V_{GS} =-3.3V)	< 22mΩ
$R_{DS(ON)}$ (at V_{GS} =-2.5V)	< 26mΩ
$R_{DS(ON)}$ (at V_{GS} =-1.8V)	< 36mΩ
$R_{DS(ON)}$ (at V_{GS} =-1.5V)	< 50mΩ

100% UIS Tested
100% R_g Tested

SOIC-8





Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-12	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current	T_A=25℃	I_D	-9	A
	T_A=70℃		-7	
Pulsed Drain Current [C]		I_{DM}	-55	
Avalanche Current [C]		I_{AS}	20	A
Avalanche energy L=0.1mH [C]		E_{AS}	20	mJ
Power Dissipation [B]	T_A=25℃	P_D	2.5	W
	T_A=70℃		1.6	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	℃

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	42	50	℃/W
Maximum Junction-to-Ambient [A D]	Steady-State		70	85	℃/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	20	30	℃/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-12			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-12V, V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±8V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250µA	-0.3	-0.6	-0.9	V
$I_{D(ON)}$	On state drain current	V_{GS}=-4.5V, V_{DS}=-5V	-55			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-4.5V, I_D=-9A		15	19	mΩ
		T_J=125°C		19.5	25	
		V_{GS}=-3.3V, I_D=-7A		17	22	mΩ
		V_{GS}=-2.5V, I_D=-6A		20	26	mΩ
		V_{GS}=-1.8V, I_D=-4A		27	36	mΩ
		V_{GS}=-1.5V, I_D=-1A		33	50	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-9A		-33		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V		-0.6	-1	V
I_S	Maximum Body-Diode Continuous Current				-3.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-6V, f=1MHz		1370		pF
C_{oss}	Output Capacitance			350		pF
C_{rss}	Reverse Transfer Capacitance			258		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		10	20	Ω
SWITCHING PARAMETERS						
Q_g(4.5V)	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-6V, I_D=-9A		12.7	18	nC
Q_{gs}	Gate Source Charge			1.7		nC
Q_{gd}	Gate Drain Charge			3.4		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-4.5V, V_{DS}=-6V, R_L=0.67Ω, R_{GEN}=3Ω		11		ns
t_r	Turn-On Rise Time			25		ns
$t_{D(off)}$	Turn-Off DelayTime			70		ns
t_f	Turn-Off Fall Time			41.5		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-9A, dI/dt=100A/µs		20.7		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-9A, dI/dt=100A/µs		5.2		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initialT_J=25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

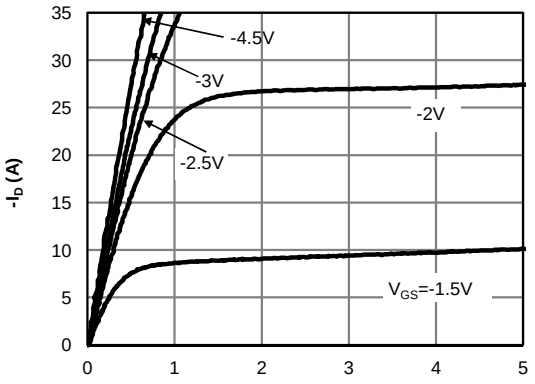


Fig 1: On-Region Characteristics (Note E)

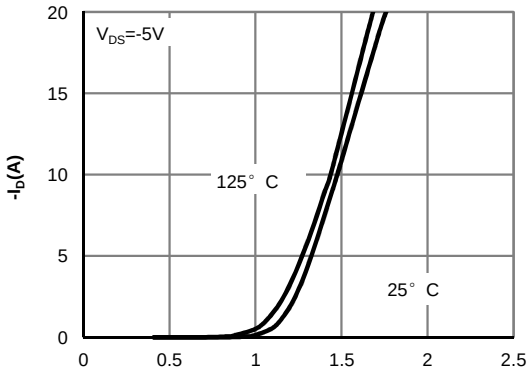


Figure 2: Transfer Characteristics (Note E)

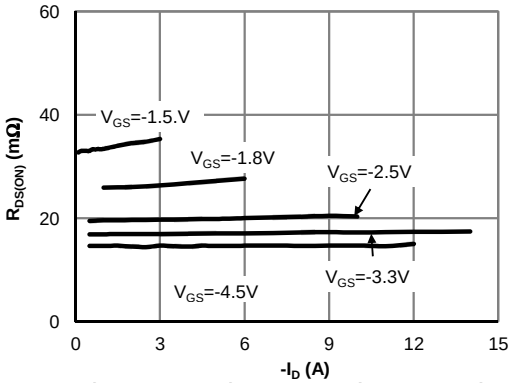


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

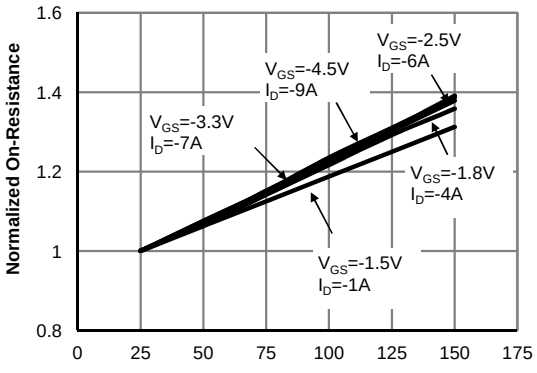


Figure 4: On-Resistance vs. Junction Temperature (Note E)

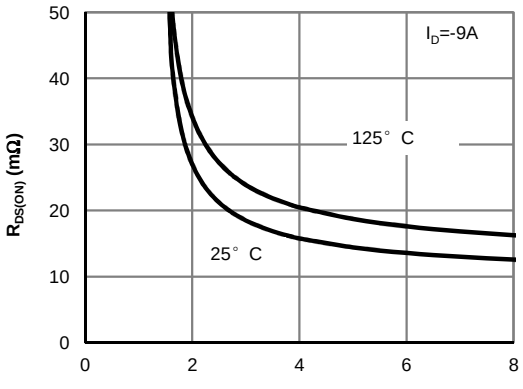


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

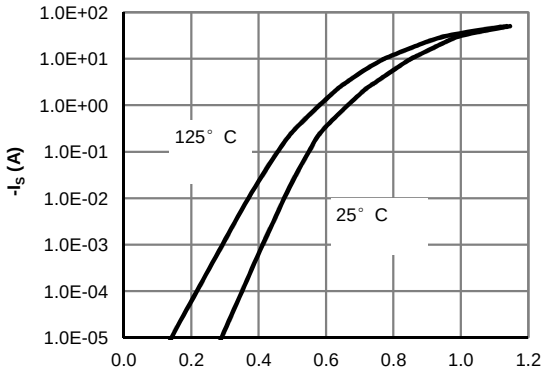


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

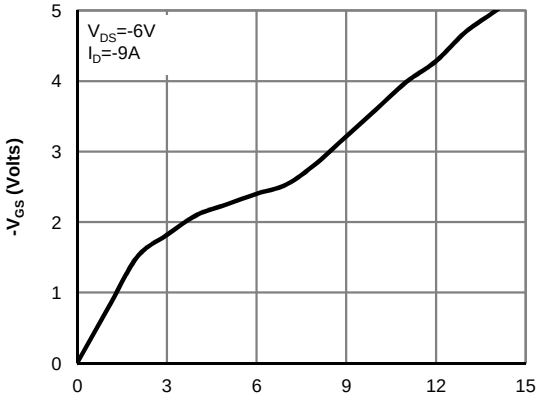


Figure 7: Gate-Charge Characteristics

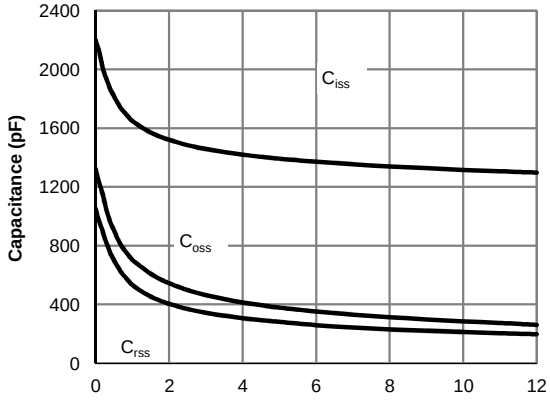


Figure 8: Capacitance Characteristics

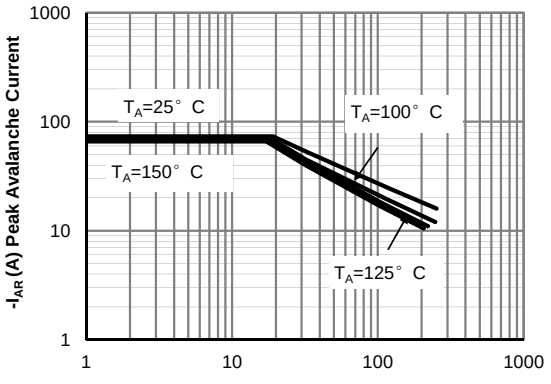


Figure 9: Single Pulse Avalanche capability (Note C)

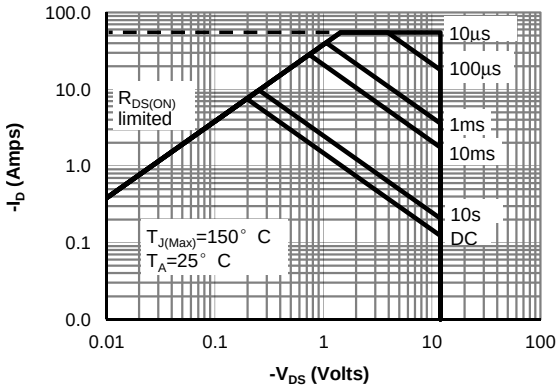


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

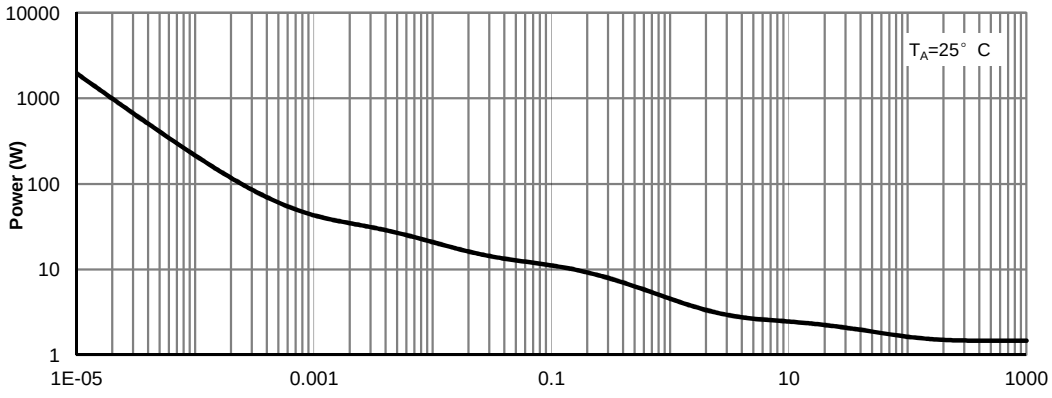


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

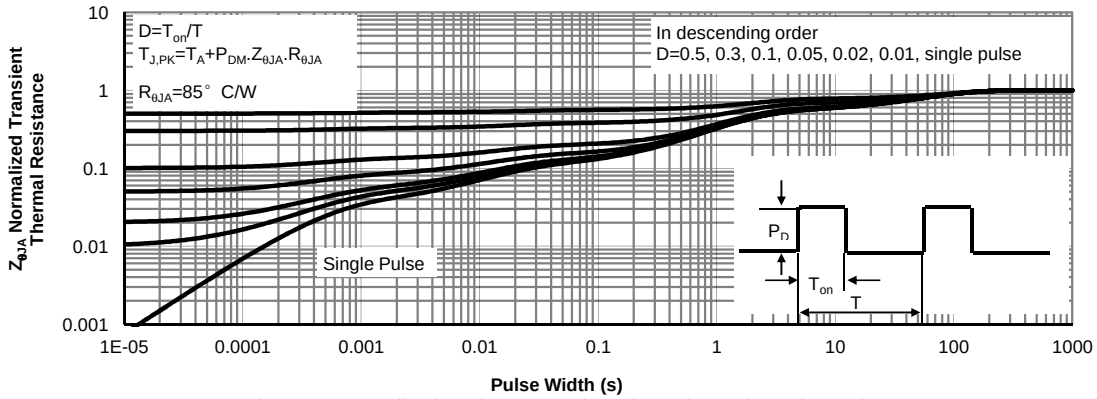
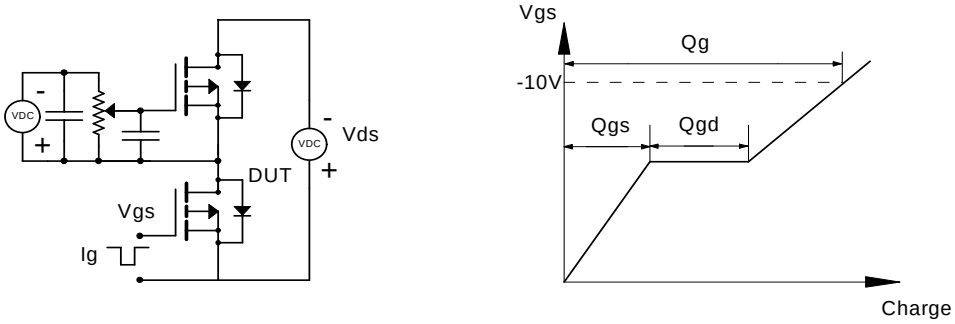
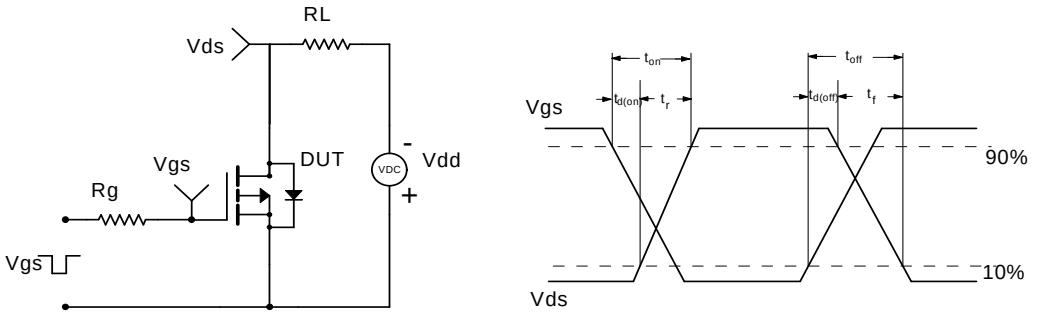


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

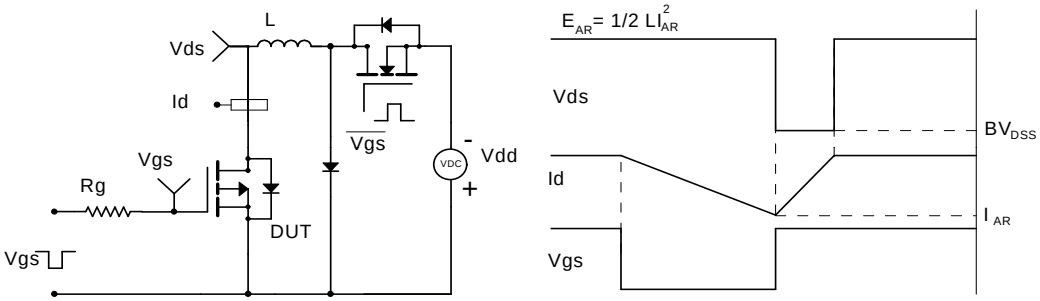
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms